

Vishay Semiconductors



Small Signal Fast Switching Diodes

Features

- Silicon Epitaxial Planar Diode
- · Low forward voltage drop
- AEC-Q101 qualified
- High forward current capability
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
 FREE
- Halogen-free according to IEC 61249-2-21 definition

Applications

• High speed switch and general purpose use in computer and industrial applications

Mechanical Data

Case: DO-35 Weight: approx. 125 mg Cathode band color: black



Packaging codes/options:

TR/10 k per 13" reel (52 mm tape), 50 k/box TAP/10 k per Ammopack (52 mm tape), 50 k/box

Parts Table

Part	Ordering code	Type Marking	Remarks
1N4150	1N4150-TR or 1N4150-TAP	1N4150	Tape and Reel/Ammopack

RoHS

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		V _{RRM}	50	V
Reverse voltage		V _R	50	V
Peak forward surge current	t _p = 1 μs	I _{FSM}	4	A
Average peak forward current		I _{FRM}	600	mA
Forward continuous current		١ _F	300	mA
Average forward current	V _R = 0	I _{FAV}	150	mA
Power dissipation	l = 4 mm, T _L = 45 °C	P _{tot}	440	mW
	l = 4 mm, $T_L \le 25 \ ^\circ C$	P _{tot}	500	mW

Thermal Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air	$I = 4 \text{ mm}, T_L = \text{constant}$	R _{thJA}	350	K/W
Junction temperature		Тj	175	°C
Storage temperature range		T _{stg}	- 65 to + 175	°C

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Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min.	Тур.	Max.	Unit
Forward voltage	I _F = 1 mA	V _F	540		620	mV
	I _F = 10 mA	V _F	660		740	mV
	I _F = 50 mA	V _F	760		860	mV
	l _F = 100 mA	V _F	820		920	mV
	l _F = 200 mA	V _F	870		1000	mV
Reverse current	V _R = 50 V	I _R			100	nA
	V _R = 50 V, T _j = 150 °C	I _R			100	μA
Diode capacitance	$V_{R} = 0, f = 1 \text{ MHz}, V_{HF} = 50 \text{ mV}$	CD			2.5	pF
Reverse recovery time	$I_F = I_R = (10 \text{ to } 100) \text{ mA}, i_R = 0.1$ x I _R , R _L = 100 Ω	t _{rr}			4	ns

Typical Characteristics

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

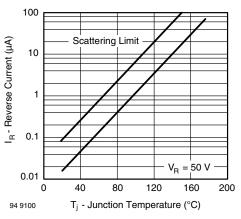
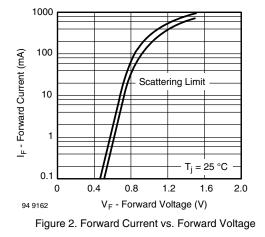
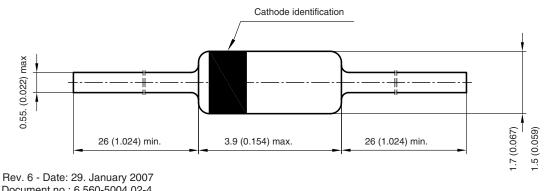


Figure 1. Reverse Current vs. Junction Temperature

Package Dimensions in mm (inches): DO-35





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